

MOSFET

OptiMOS™ 5 Linear FET 2, 100 V

Features

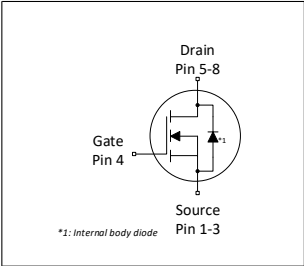
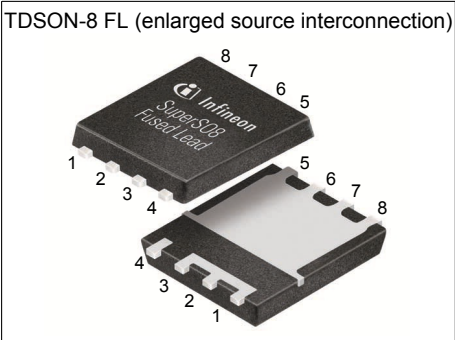
- Ideal for hot-swap, battery protection and e-fuse applications
- Very low on-resistance $R_{DS(on)}$
- Wide safe operating area SOA
- N-channel, normal level
- 100% avalanche tested
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

Product validation

Fully qualified according to JEDEC for Industrial Applications

Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	100	V
$R_{DS(on),max}$	3.5	mΩ
I_D	164	A
$I(V_{DS}=50\text{ V}, t_p=10\text{ ms})$	5.2	A



RoHS

Type / Ordering Code	Package	Marking	Related Links
ISC035N10NM5LF2	PG-TDSON-8 FL	35N10LF2	-

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1 Maximum ratings

at $T_A=25\text{ °C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	164 116 19	A	$V_{GS}=10\text{ V}$, $T_C=25\text{ °C}$ $V_{GS}=10\text{ V}$, $T_C=100\text{ °C}$ $V_{GS}=10\text{ V}$, $T_A=25\text{ °C}$, $R_{thJA}=50\text{ °C/W}^{2)}$
Pulsed drain current ³⁾	$I_{D,pulse}$	-	-	656	A	$T_A=25\text{ °C}$
Avalanche energy, single pulse ⁴⁾	E_{AS}	-	-	398	mJ	$I_D=50\text{ A}$, $R_{GS}=25\text{ }\Omega$
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	217 3	W	$T_C=25\text{ °C}$ $T_A=25\text{ °C}$, $R_{thJA}=50\text{ °C/W}^{2)}$
Operating and storage temperature	T_j , T_{stg}	-55	-	175	°C	-

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case, bottom	R_{thJC}	-	-	0.7	°C/W	-
Thermal resistance, junction - case, top	R_{thJC}	-	-	20	°C/W	-
Thermal resistance, junction - ambient, 6 cm ² cooling area ²⁾	R_{thJA}	-	-	50	°C/W	-

¹⁾ Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature as specified. For other case temperatures please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.

²⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

³⁾ See Diagrams 3 and 4 for more detailed information

⁴⁾ See Diagram 14 for more detailed information

3 Electrical characteristics

at $T_j=25\text{ °C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	100	-	-	V	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	2.3	3.1	3.9	V	$V_{DS}=V_{GS}$, $I_D=115\text{ }\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	0.1 10	1 100	μA	$V_{DS}=100\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$ $V_{DS}=100\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=125\text{ °C}$
Gate-source leakage current	I_{GSS}	-	10	100	nA	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	3.0	3.5	m Ω	$V_{GS}=10\text{ V}$, $I_D=50\text{ A}$
Gate resistance	R_G	-	1.5	2.3	Ω	-
Transconductance ¹⁾	g_{fs}	26	52	-	S	$ V_{DS} \geq 2 I_D /R_{DS(on)max}$, $I_D=50\text{ A}$

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance ¹⁾	C_{iss}	-	5500	7200	pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=1\text{ MHz}$
Output capacitance ¹⁾	C_{oss}	-	780	1000	pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=1\text{ MHz}$
Reverse transfer capacitance ¹⁾	C_{rss}	-	19	33	pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	16	-	ns	$V_{DD}=50\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=50\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Rise time	t_r	-	11	-	ns	$V_{DD}=50\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=50\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	-	25	-	ns	$V_{DD}=50\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=50\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Fall time	t_f	-	10	-	ns	$V_{DD}=50\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=50\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$

Table 6 Gate charge characteristics²⁾

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	35	-	nC	$V_{DD}=50\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge at threshold	$Q_{g(th)}$	-	17	-	nC	$V_{DD}=50\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge ¹⁾	Q_{gd}	-	12	18	nC	$V_{DD}=50\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Switching charge	Q_{sw}	-	30	-	nC	$V_{DD}=50\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total ¹⁾	Q_g	-	70	88	nC	$V_{DD}=50\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	6.4	-	V	$V_{DD}=50\text{ V}$, $I_D=50\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Output charge ¹⁾	Q_{oss}	-	90	115	nC	$V_{DS}=50\text{ V}$, $V_{GS}=0\text{ V}$

¹⁾ Defined by design. Not subject to production test.

²⁾ See "Gate charge waveforms" for parameter definition

Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	159	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	656	A	$T_C=25\text{ °C}$
Diode forward voltage	V_{SD}	-	0.84	1.2	V	$V_{GS}=0\text{ V}$, $I_F=50\text{ A}$, $T_j=25\text{ °C}$
Reverse recovery time ¹⁾	t_{rr}	-	49	98	ns	$V_R=50\text{ V}$, $I_F=50\text{ A}$, $di_F/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge ¹⁾	Q_{rr}	-	72	144	nC	$V_R=50\text{ V}$, $I_F=50\text{ A}$, $di_F/dt=100\text{ A}/\mu\text{s}$

¹⁾ Defined by design. Not subject to production test.

4 Electrical characteristics diagrams

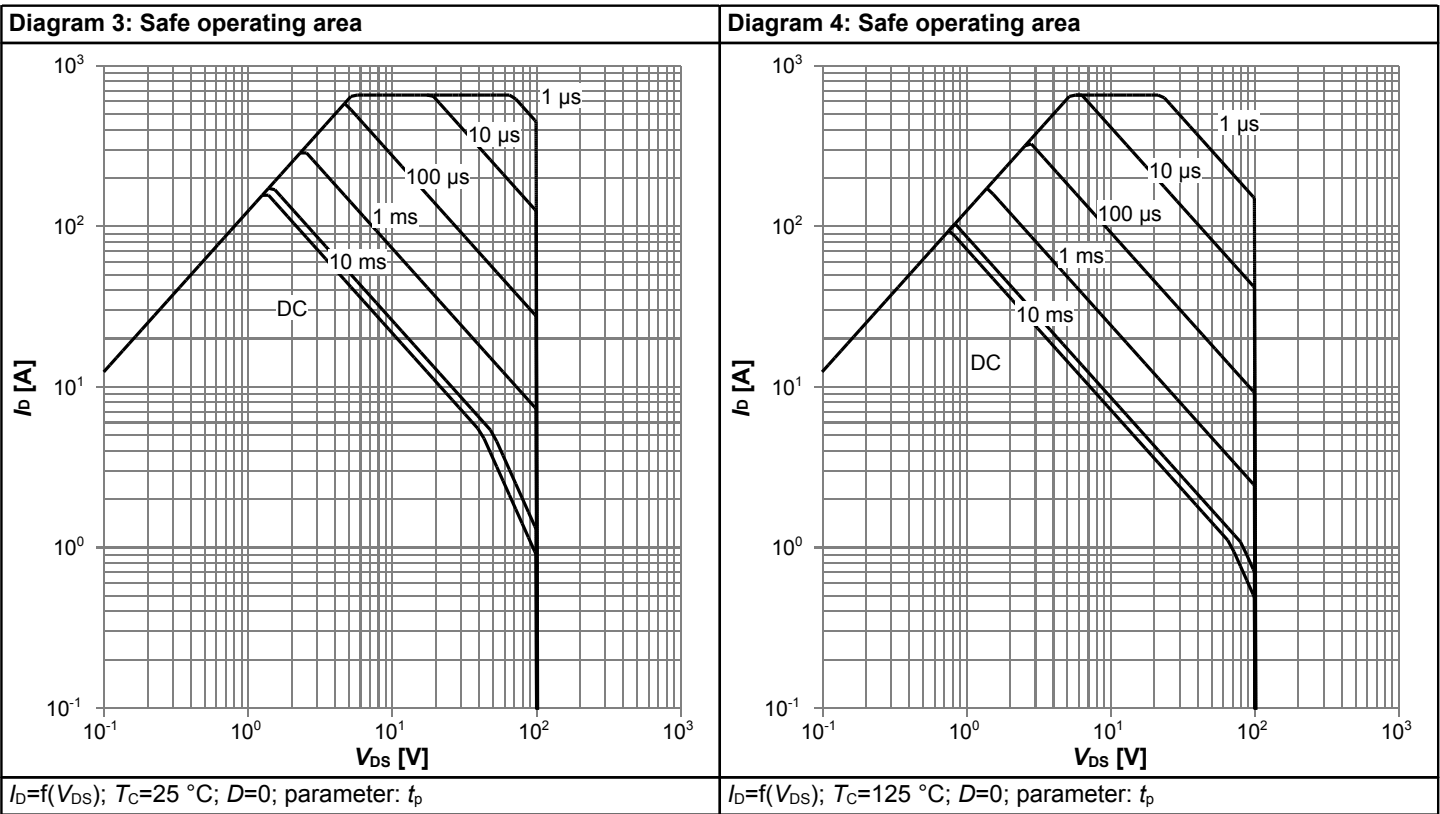
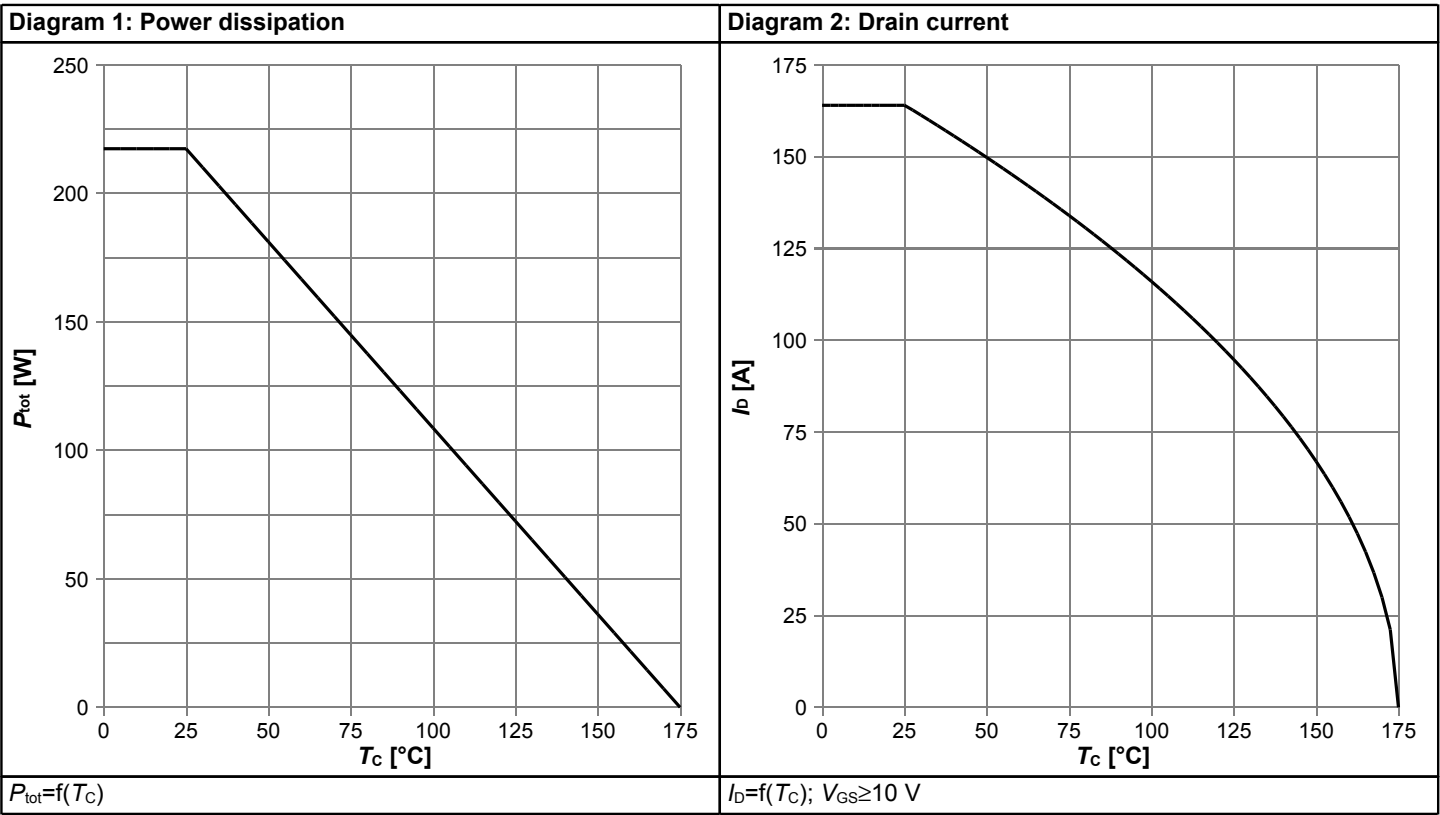
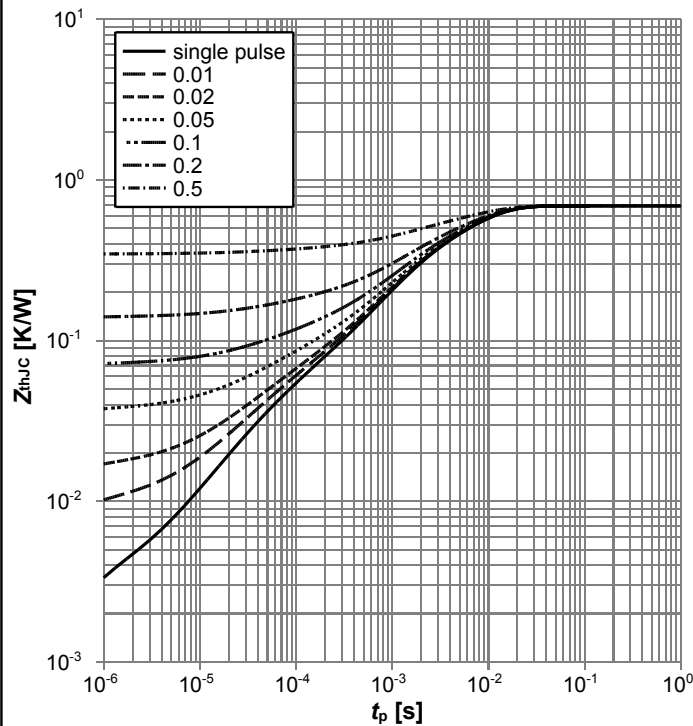
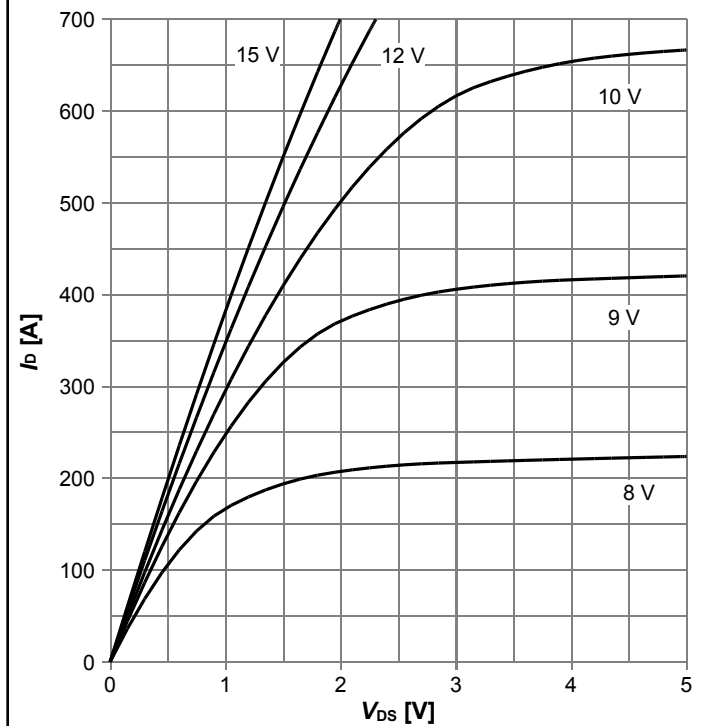


Diagram 5: Max. transient thermal impedance



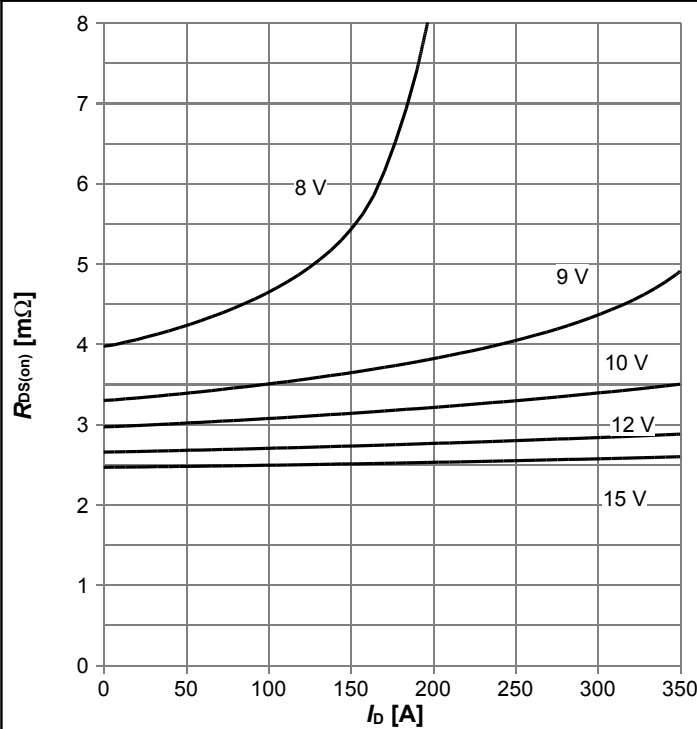
$Z_{thJC} = f(t_p)$; parameter: $D = t_p / T$

Diagram 6: Typ. output characteristics



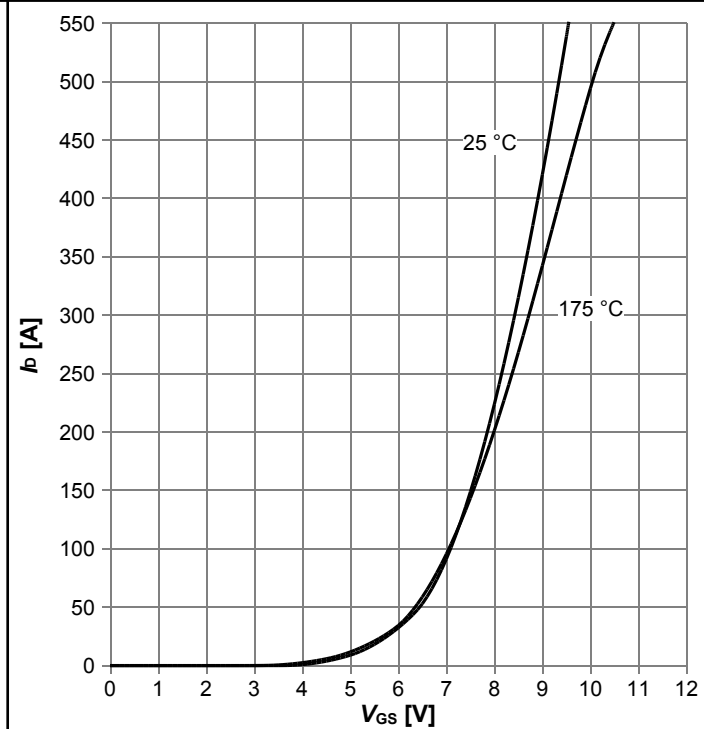
$I_D = f(V_{DS})$, $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 7: Typ. drain-source on resistance



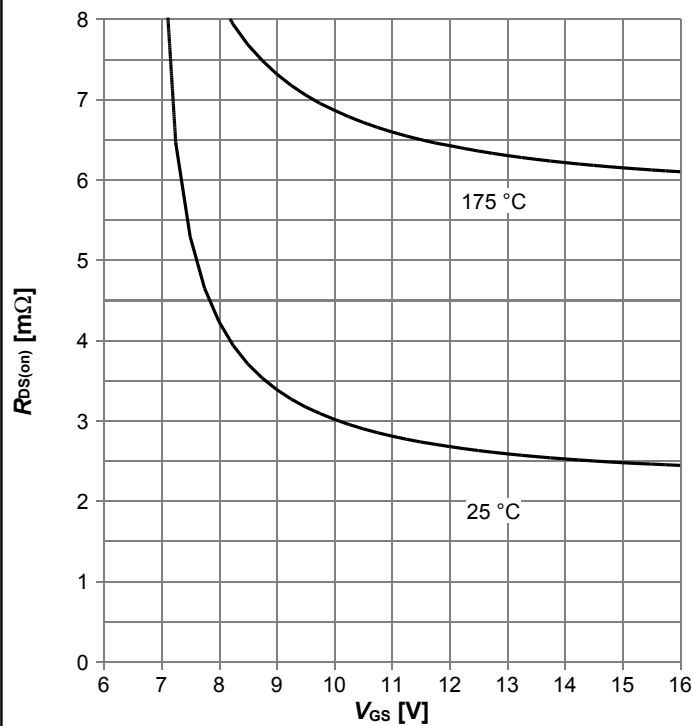
$R_{DS(on)} = f(I_D)$, $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 8: Typ. transfer characteristics



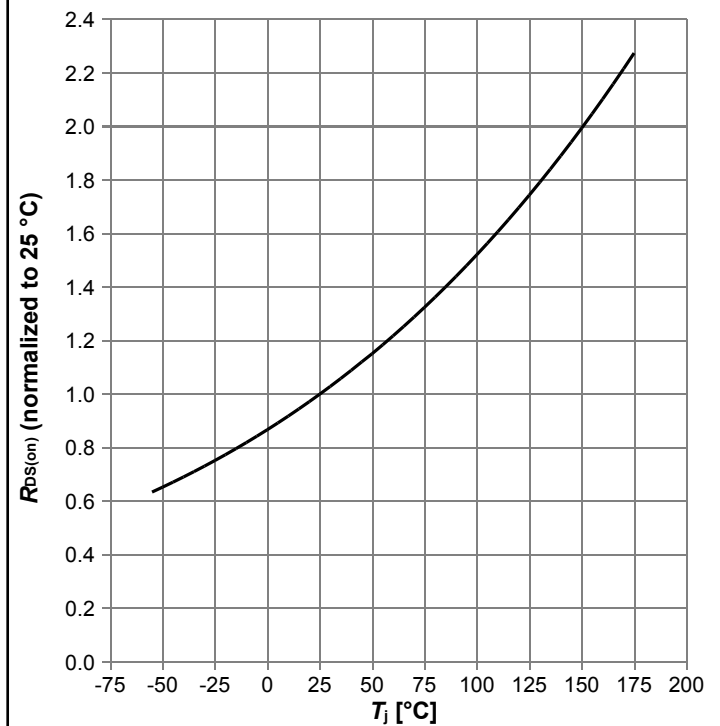
$I_D = f(V_{GS})$, $|V_{DS}| > 2|I_D|R_{DS(on)max}$; parameter: T_j

Diagram 9: Typ. drain-source on resistance



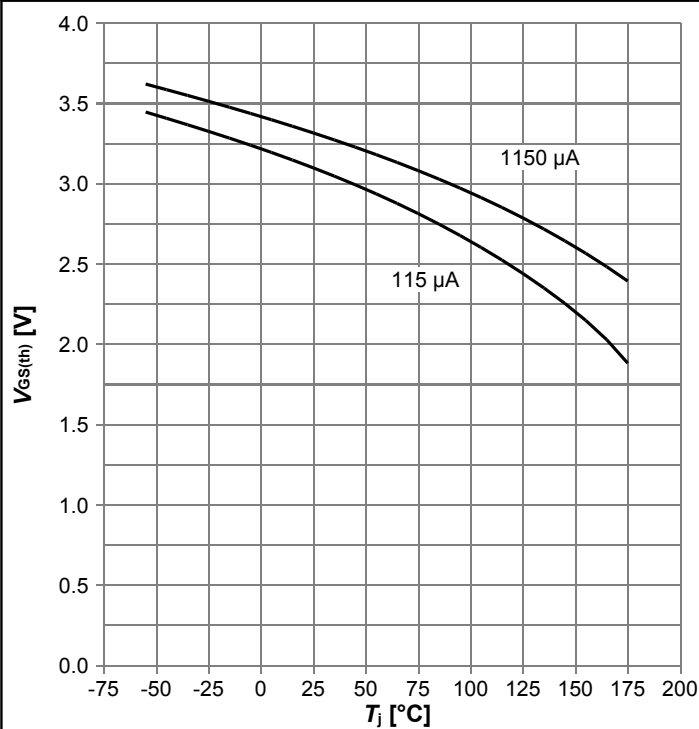
$R_{DS(on)}=f(V_{GS})$, $I_D=50$ A; parameter: T_j

Diagram 10: Normalized drain-source on resistance



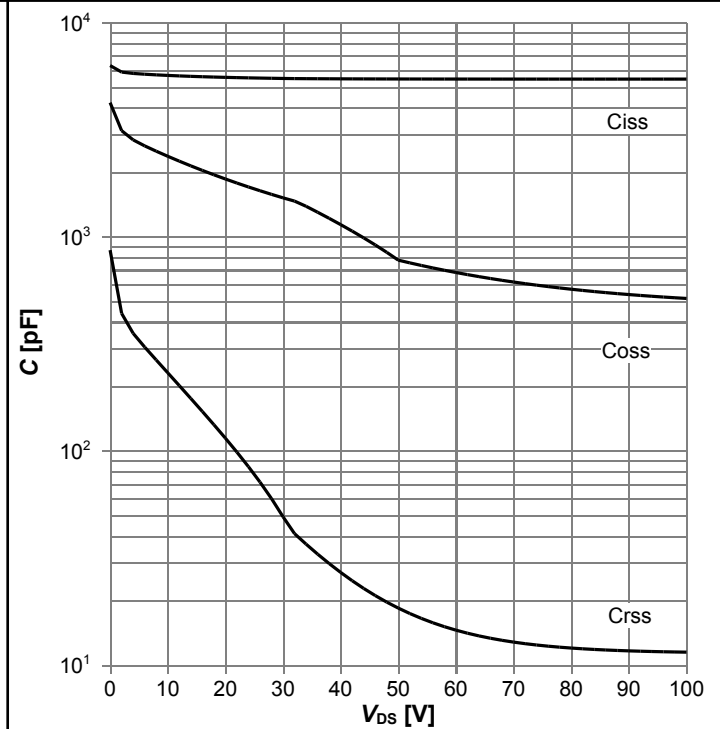
$R_{DS(on)}=f(T_j)$, $I_D=50$ A, $V_{GS}=10$ V

Diagram 11: Typ. gate threshold voltage



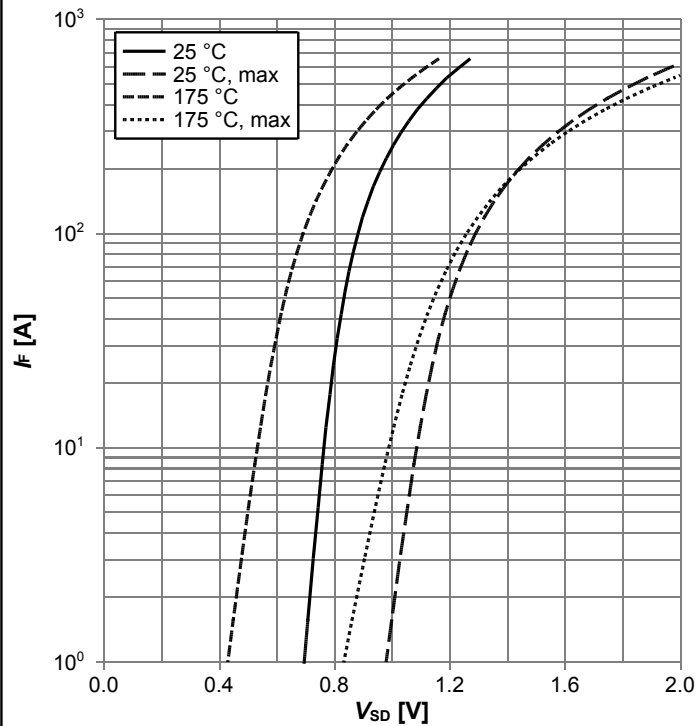
$V_{GS(th)}=f(T_j)$, $V_{GS}=V_{DS}$; parameter: I_D

Diagram 12: Typ. capacitances



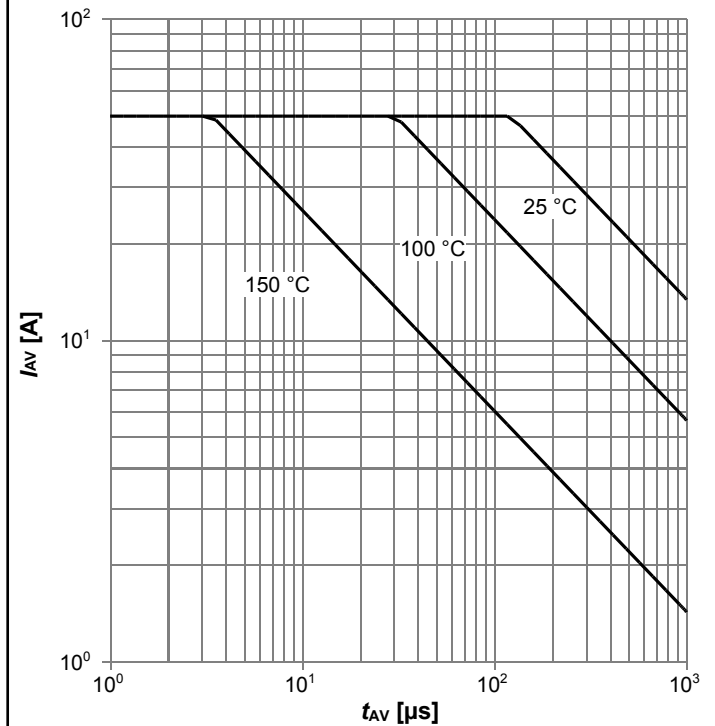
$C=f(V_{DS})$; $V_{GS}=0$ V; $f=1$ MHz

Diagram 13: Forward characteristics of reverse diode



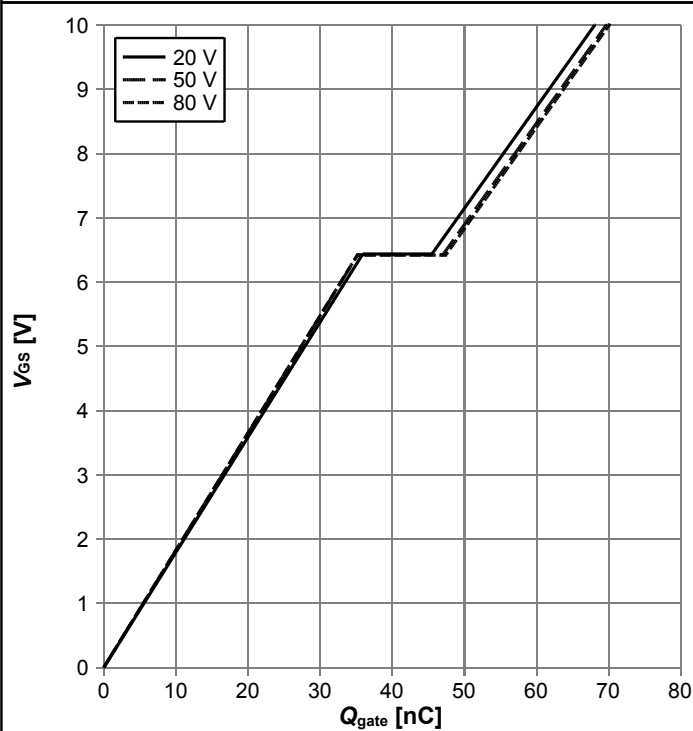
$I_F = f(V_{SD})$; parameter: T_j

Diagram 14: Avalanche characteristics



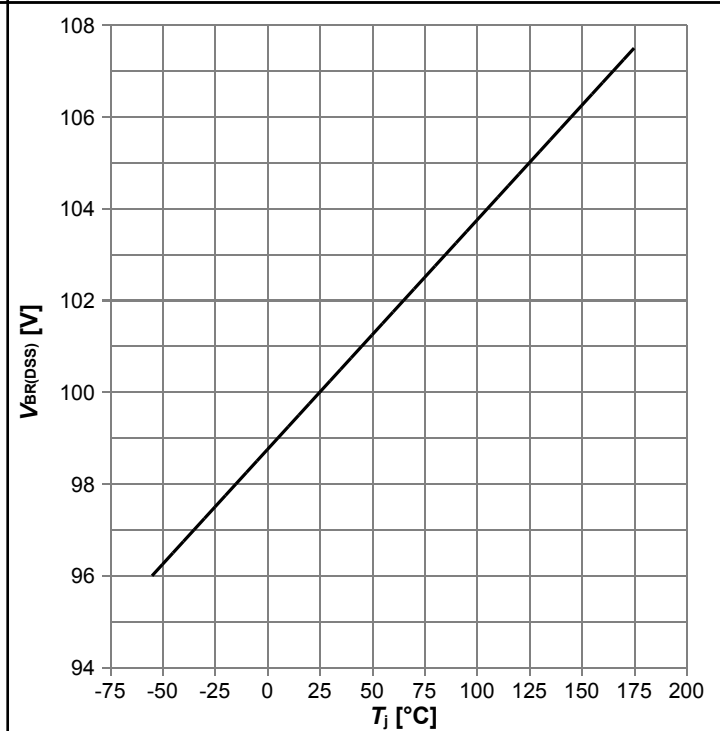
$I_{AS} = f(t_{AV})$; $R_{GS} = 25 \Omega$; parameter: $T_{j,start}$

Diagram 15: Typ. gate charge

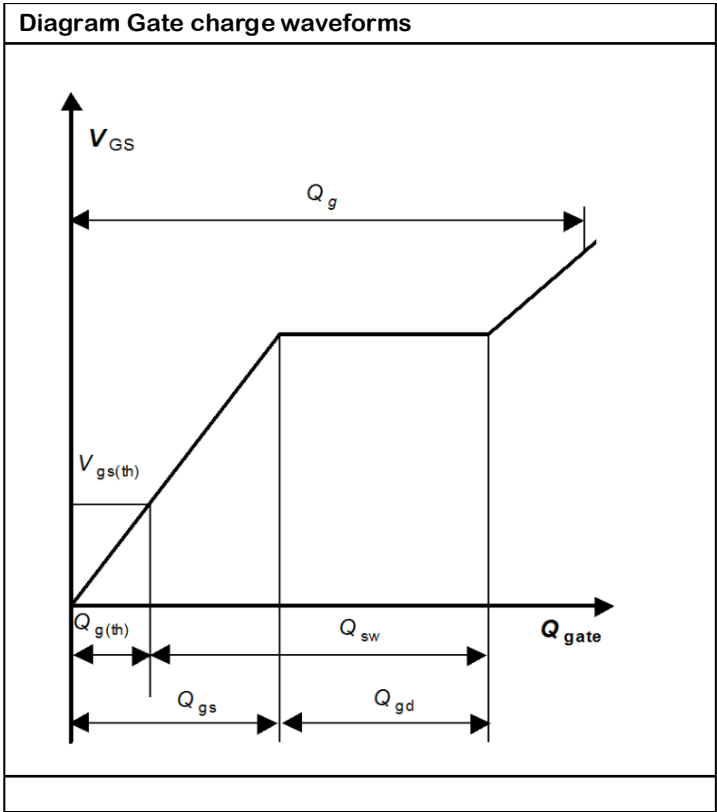


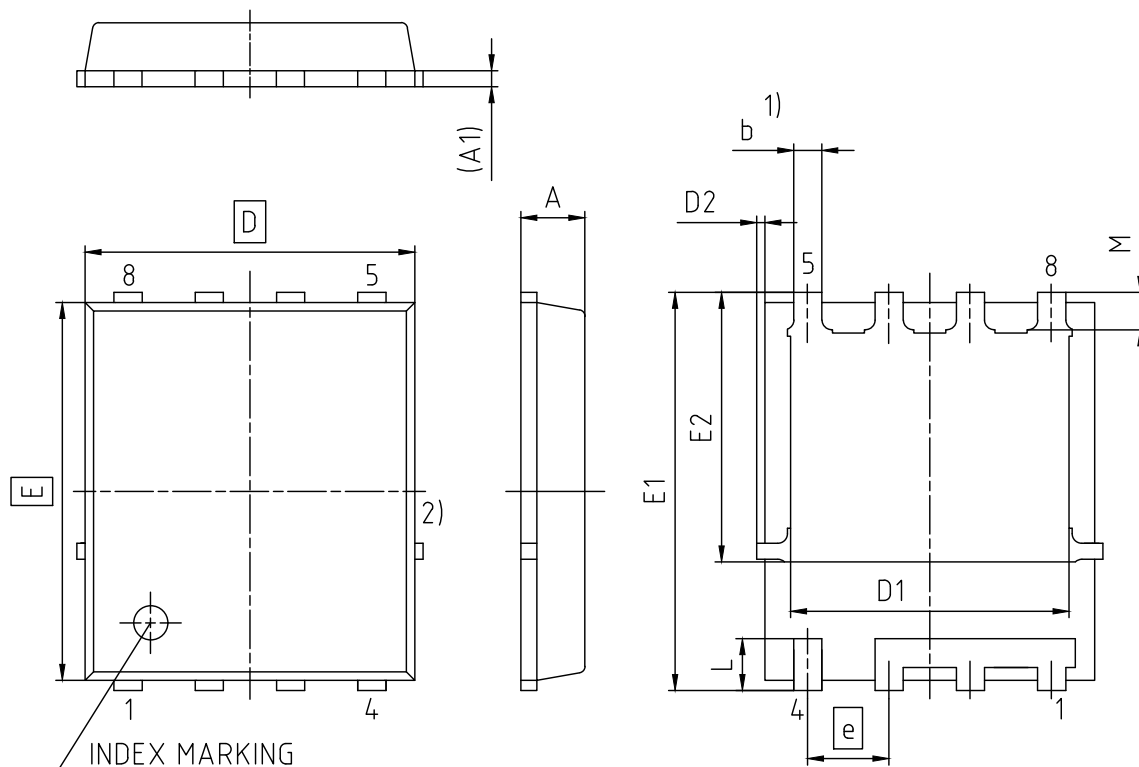
$V_{GS} = f(Q_{gate})$, $I_D = 50 \text{ A}$ pulsed, $T_j = 25 \text{ °C}$; parameter: V_{DD}

Diagram 16: Drain-source breakdown voltage



$V_{BR(DSS)} = f(T_j)$; $I_D = 1 \text{ mA}$





DIMENSION	MILLIMETERS	
	MIN.	MAX.
A	0.90	1.20
A1	0.15	0.35
b	0.26	0.54
D	4.80	5.35
D1	3.70	4.40
D2	0.00	0.23
E	5.70	6.10
E1	5.90	6.42
E2	3.88	4.42
e	1.27	
L	0.69	0.90
M	0.45	0.69

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ISC035N10NM5LF2

Revision: 2023-11-08, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.1	2023-11-08	Update sales name and marking

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